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	APPLICANT	KERBER		
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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

								TRANSLATION	
		DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

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EXAMINER	DATE CONSIDERED
<i>[Signature]</i>	8/19/04